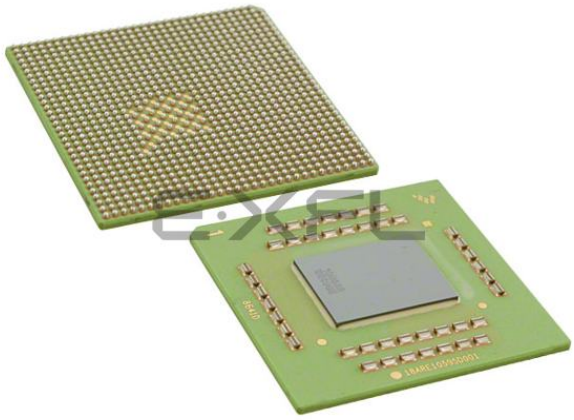

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641thx1000gc

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8641. The MPC8641 is currently targeted to these specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic	Symbol	Absolute Maximum Value	Unit	Notes
Cores supply voltages	V_{DD}_Core0, V_{DD}_Core1	–0.3 to 1.21 V	V	2
Cores PLL supply	AV_{DD}_Core0, AV_{DD}_Core1	–0.3 to 1.21 V	V	—
SerDes Transceiver Supply (Ports 1 and 2)	SV_{DD}	–0.3 to 1.21 V	V	—
SerDes Serial I/O Supply Port 1	XV_{DD}_SRDS1	–0.3 to 1.21V	V	—
SerDes Serial I/O Supply Port 2	XV_{DD}_SRDS2	–0.3 to 1.21 V	V	—
SerDes DLL and PLL supply voltage for Port 1 and Port 2	AV_{DD}_SRDS1, AV_{DD}_SRDS2	–0.3 to 1.21V	V	—
Platform Supply voltage	V_{DD}_PLAT	–0.3 to 1.21V	V	—
Local Bus and Platform PLL supply voltage	AV_{DD}_LB, AV_{DD}_PLAT	–0.3 to 1.21V	V	—
DDR and DDR2 SDRAM I/O supply voltages	D1_GV_{DD}, D2_GV_{DD}	–0.3 to 2.75 V	V	3
		–0.3 to 1.98 V	V	3
eTSEC 1 and 2 I/O supply voltage	LV_{DD}	–0.3 to 3.63 V	V	4
		–0.3 to 2.75 V	V	4
eTSEC 3 and 4 I/O supply voltage	TV_{DD}	–0.3 to 3.63 V	V	4
		–0.3 to 2.75 V	V	4
Local Bus, DUART, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{DD}	–0.3 to 3.63 V	V	—

Table 2. Recommended Operating Conditions (continued)

Characteristic		Symbol	Recommended Value	Unit	Notes
SerDes Serial I/O Supply Port 1		XV_{DD}_SRDS1	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
SerDes Serial I/O Supply Port 2		XV_{DD}_SRDS2	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
SerDes DLL and PLL supply voltage for Port 1 and Port 2		AV_{DD}_SRDS1, AV_{DD}_SRDS2	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
Platform Supply voltage		V_{DD}_PLAT	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
Local Bus and Platform PLL supply voltage		AV_{DD}_LB, AV_{DD}_PLAT	1.10 ± 50 mV	V	8
			1.05 ± 50 mV		7
DDR and DDR2 SDRAM I/O supply voltages		D1_GV_{DD}, D2_GV_{DD}	2.5 V ± 125 mV	V	9
			1.8 V ± 90 mV	V	9
eTSEC 1 and 2 I/O supply voltage		LV_{DD}	3.3 V ± 165 mV	V	10
			2.5 V ± 125 mV	V	10
eTSEC 3 and 4 I/O supply voltage		TV_{DD}	3.3 V ± 165 mV	V	10
			2.5 V ± 125 mV	V	10
Local Bus, DUART, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I^2C, JTAG and Miscellaneous I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	5
Input voltage	DDR and DDR2 SDRAM signals	D*n*_MV_{IN}	GND to D*n*_GV_{DD}	V	3, 6
	DDR and DDR2 SDRAM reference	D*n*_MV_{REF}	D*n*_GV_{DD}/2 ± 1%	V	
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4, 6
	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{IN}	GND to OV_{DD}	V	5,6

Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	T_J	0 to 105	°C	—

Notes:

1. Core 1 characteristics apply only to MPC8641D
2. If two separate power supplies are used for V_{DD}_Core0 and V_{DD}_Core1, they must be at the same nominal voltage and the individual power supplies must be tracked and kept within 100 mV of each other during normal run time.
3. **Caution:** D*n*_MV_{IN} must meet the overshoot/undershoot requirements for D*n*_GV_{DD} as shown in Figure 2.
4. **Caution:** L/TV_{IN} must meet the overshoot/undershoot requirements for L/TV_{DD} as shown in Figure 2 during regular run time.
5. **Caution:** OV_{IN} must meet the overshoot/undershoot requirements for OV_{DD} as shown in Figure 2 during regular run time.
6. Timing limitations for M,L,T,O)V_{IN} and D*n*_MV_{REF} during regular run time is provided in Figure 2
7. Applies to devices marked with a core frequency of 1333 MHz and below. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for a core frequency of 1333 MHz and below.
8. Applies to devices marked with a core frequency above 1333 MHz. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for a core frequency above 1333 MHz.
9. The 2.5 V ± 125 mV range is for DDR and 1.8 V ± 90 mV range is for DDR2.
10. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
11. The PCI Express interface of the device is expected to receive signals from 0.175 to 1.2 V. For more information refer to Section 14.4.3, "Differential Receiver (RX) Input Specifications."
12. Applies to Part Number MC8641xxx1000NX only. V_{DD}_Core*n* = 0.95 V and V_{DD}_PLAT = 1.05 V devices. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for V_{DD}_Core*n* = 0.95 V.
13. This voltage is the input to the filter discussed in Section 20.2, "Power Supply Design and Sequencing," and not necessarily the voltage at the AV_{DD}_Core*n* pin, which may be reduced from V_{DD}_Core*n* by the filter.

Figure 4 shows the DDR SDRAM input timing for the MDQS to MDQ skew measurement (tDISKEW).

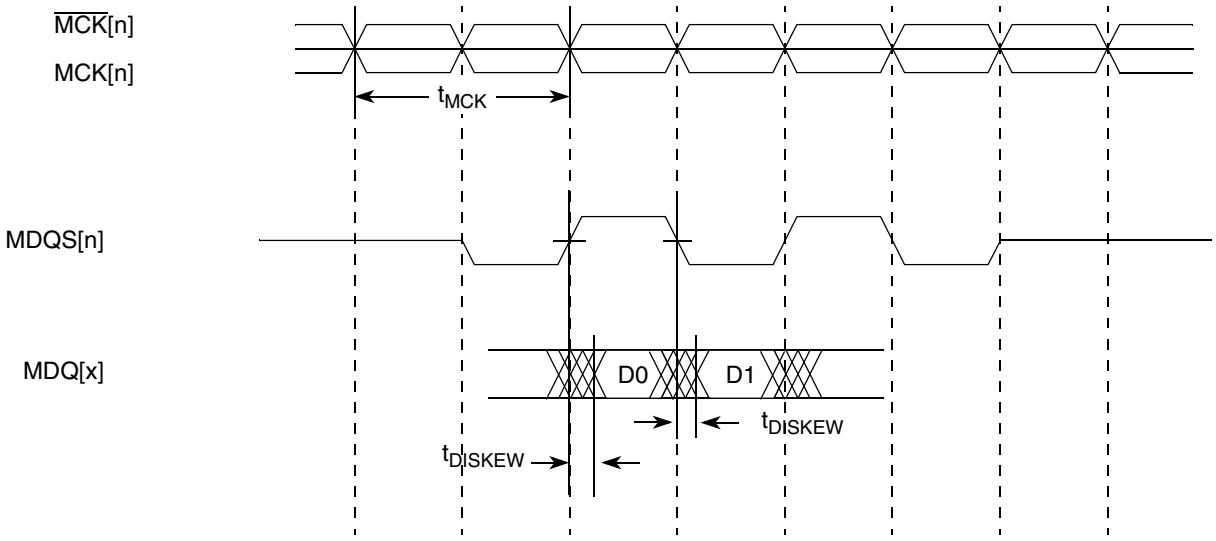

Figure 4. DDR Input Timing Diagram for tDISKEW

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 21. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[n]/MCK[n] crossing	t_{MCK}	3	10	ns	2
MCK duty cycle	t_{MCKH}/t_{MCK}			%	
600 MHz		47.5	52.5		8
533 MHz		47	53		9
400 MHz		47	53		9
ADDR/CMD output setup with respect to MCK	t_{DDKHAS}			ns	3
600 MHz		1.10	—		7
533 MHz		1.48	—		7
400 MHz		1.95	—		
ADDR/CMD output hold with respect to MCK	t_{DDKHAX}			ns	3
600 MHz		1.10	—		7
533 MHz		1.48	—		7
400 MHz		1.95	—		
MCS[n] output setup with respect to MCK	t_{DDKHCS}			ns	3
600 MHz		1.10	—		7
533 MHz		1.48	—		7
400 MHz		1.95	—		

Figure 5 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (tDDKHMH).

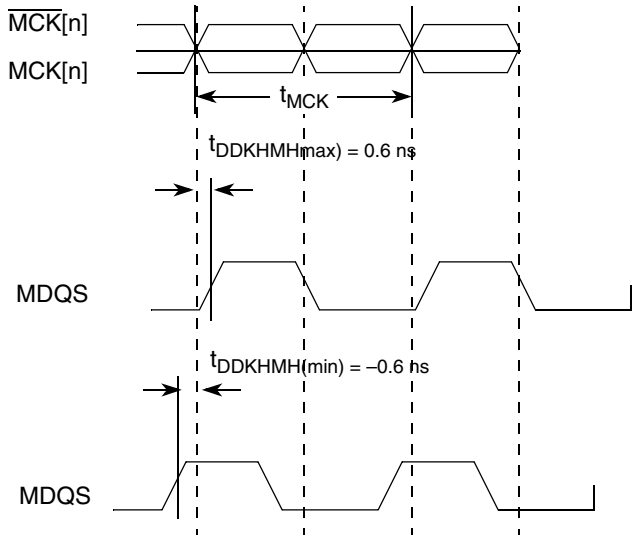

Figure 5. Timing Diagram for tDDKHMH

Figure 6 shows the DDR SDRAM output timing diagram.

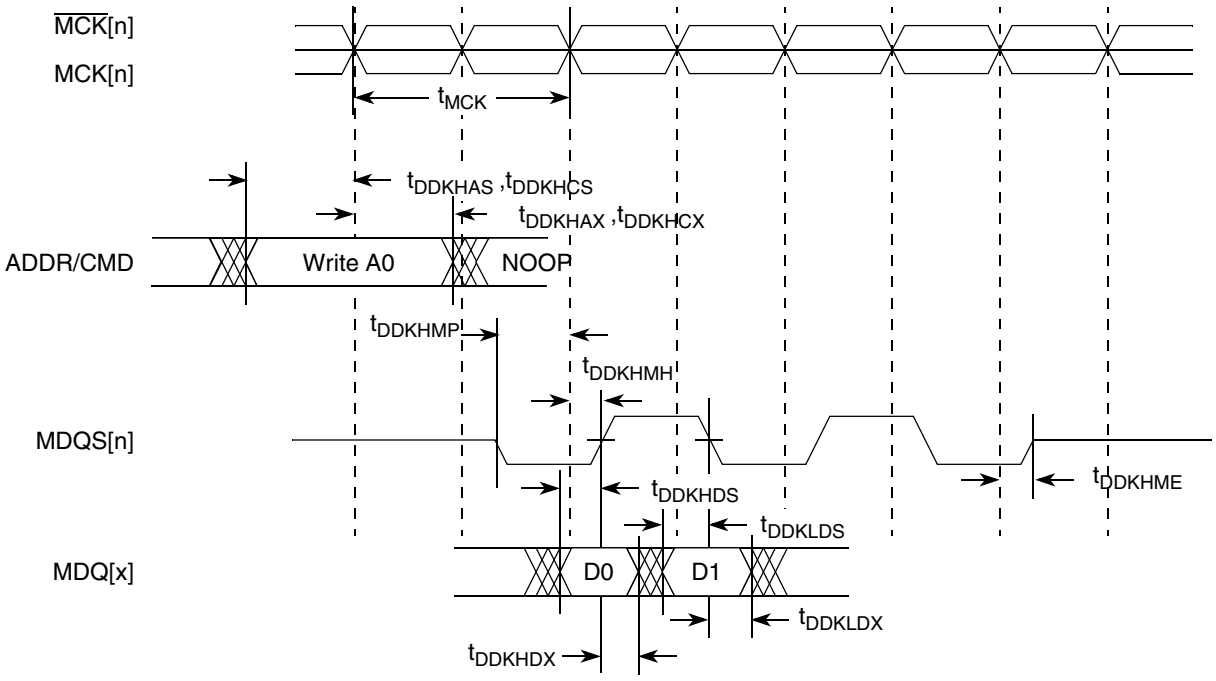

Figure 6. DDR SDRAM Output Timing Diagram

Table 29. GMII Receive AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock fall time (80%-20%)	t_{GRXF}[2]	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.
3. ±100 ppm tolerance on RX_CLK frequency

Figure 11 provides the AC test load for eTSEC.

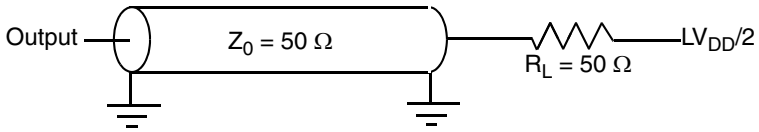

Figure 11. eTSEC AC Test Load

Figure 12 shows the GMII receive AC timing diagram.

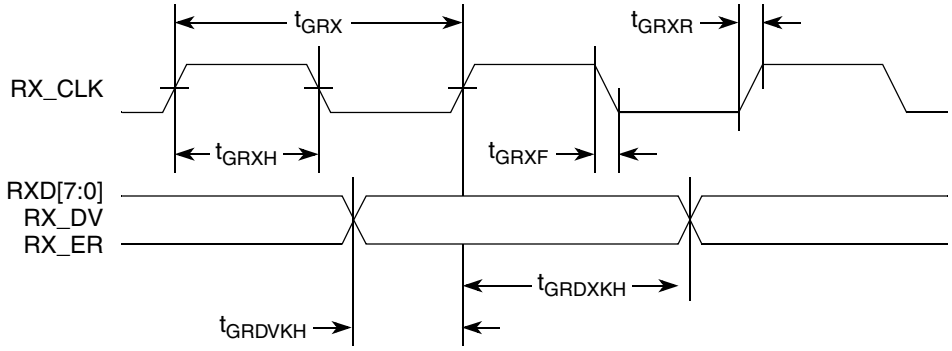

Figure 12. GMII Receive AC Timing Diagram

8.2.3.2 MII Receive AC Timing Specifications

Table 31 provides the MII receive AC timing specifications.

Table 31. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}[2,3]	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}[3]	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time (20%-80%)	t_{MRXR}[2]	1.0	—	4.0	ns
RX_CLK clock fall time (80%-20%)	t_{MRXF}[2]	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.
3. ±100 ppm tolerance on RX_CLK frequency

Figure 14 provides the AC test load for eTSEC.

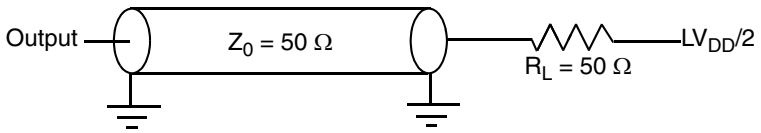

Figure 14. eTSEC AC Test Load

Figure 15 shows the MII receive AC timing diagram.

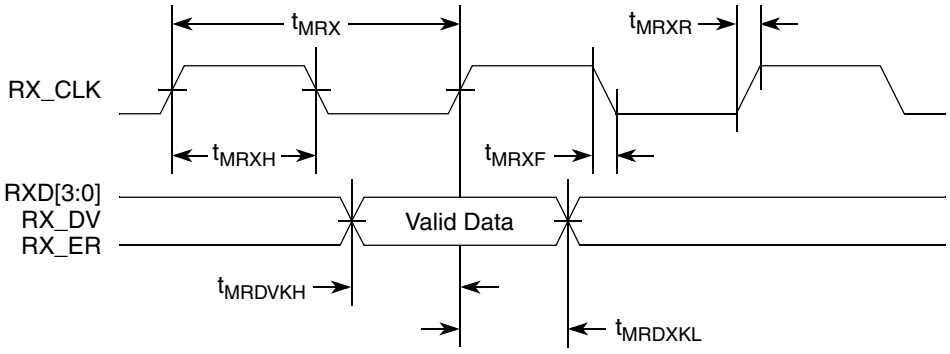

Figure 15. MII Receive AC Timing Diagram

8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

8.2.4.1 TBI Transmit AC Timing Specifications

Table 32 provides the TBI transmit AC timing specifications.

Table 32. TBI Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TCG[9:0] setup time GTX_CLK going high	t_{TTKHDV}	2.0	—	—	ns
TCG[9:0] hold time from GTX_CLK going high	t_{TTKHDX}	1.0	—	—	ns
GTX_CLK rise time (20%–80%)	t_{TTXR}[2]	—	—	1.0	ns
GTX_CLK fall time (80%–20%)	t_{TTXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 16 shows the TBI transmit AC timing diagram.

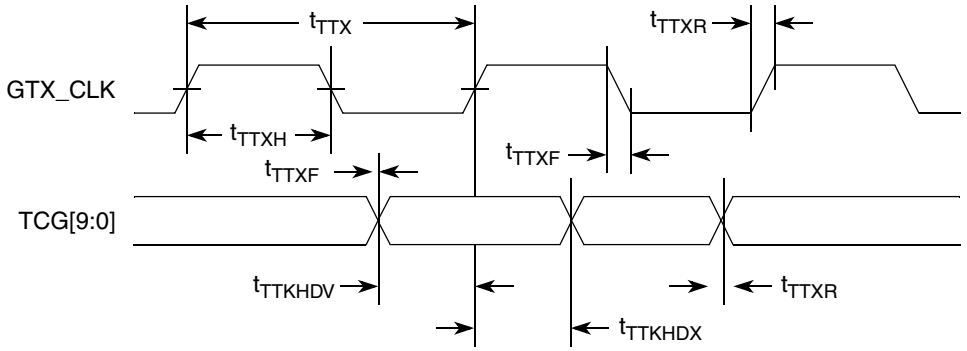

Figure 16. TBI Transmit AC Timing Diagram

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled (continued)

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	—
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

Figure 25 provides the AC test load for the local bus.

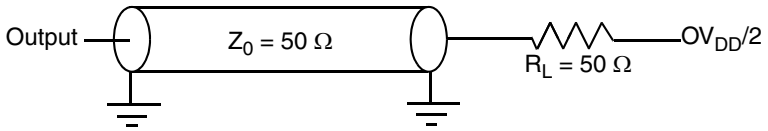

Figure 25. Local Bus AC Test Load

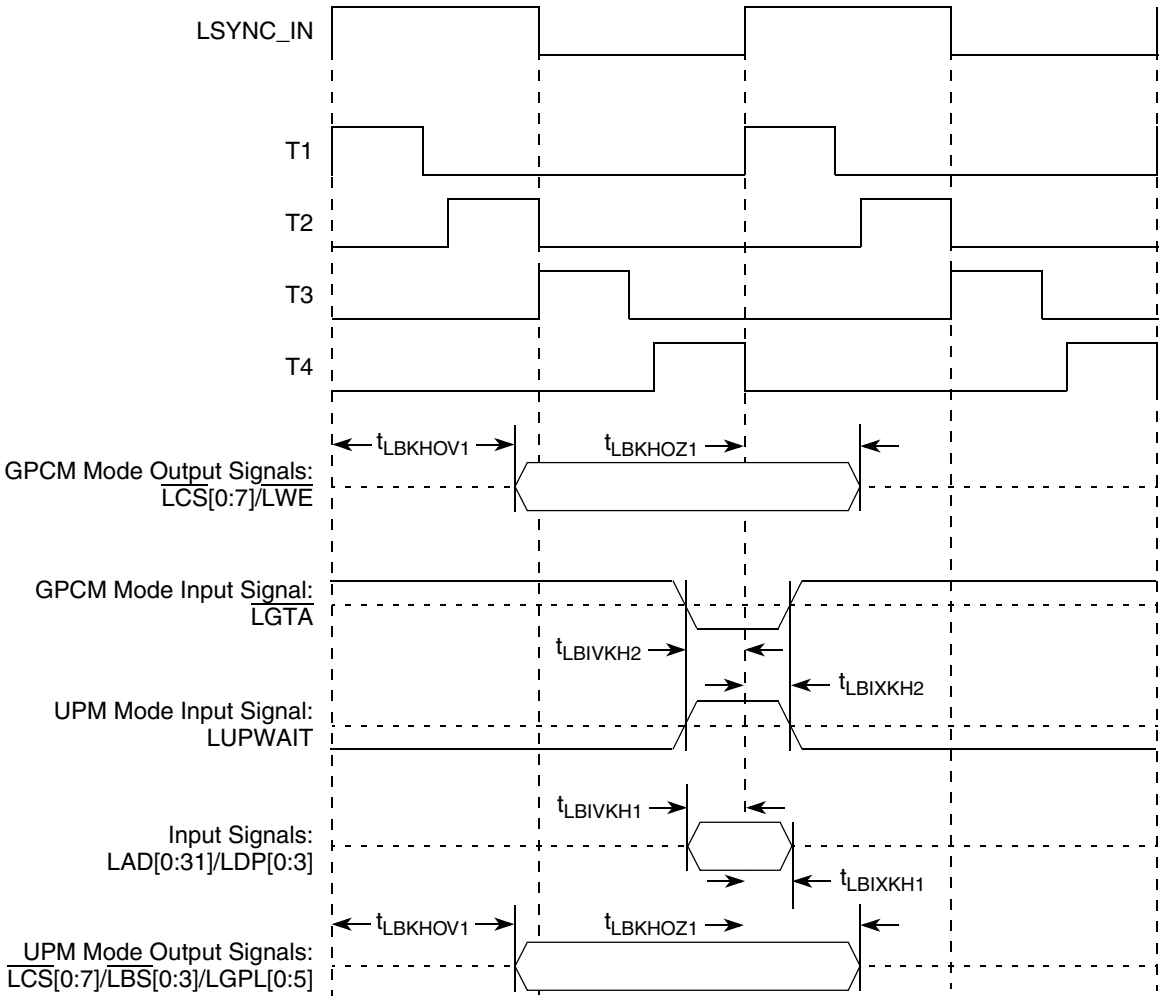

Figure 30. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 or 8 (clock ratio of 8 or 16) (PLL Enabled)

Table 46. I²C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 45).

Parameter	Symbol [1]	Min	Max	Unit
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. As a transmitter, the MPC8641 provides a delay time of at least 300 ns for the SDA signal (referred to the Vihmin of the SCL signal) to bridge the undefined region of the falling edge of SCL to avoid unintended generation of Start or Stop condition. When MPC8641 acts as the I²C bus master while transmitting, MPC8641 drives both SCL and SDA. As long as the load on SCL and SDA are balanced, MPC8641 would not cause unintended generation of Start or Stop condition. Therefore, the 300 ns SDA output delay time is not a concern. If, under some rare condition, the 300 ns SDA output delay time is required for MPC8641 as transmitter, the following setting is recommended for the FDR bit field of the I2CFDR register to ensure both the desired I²C SCL clock frequency and SDA output delay time are achieved, assuming that the desired I²C SCL clock frequency is 400 KHz and the Digital Filter Sampling Rate Register (I2CDFSRR) is programmed with its default setting of 0x10 (decimal 16):

I²C Source Clock Frequency	333 MHz	266 MHz	200 MHz	133 MHz
FDR Bit Setting	0x2A	0x05	0x26	0x00
Actual FDR Divider Selected	896	704	512	384
Actual I²C SCL Frequency Generated	371 KHz	378 KHz	390 KHz	346 KHz

   For the detail of I²C frequency calculation, refer to the application note AN2919 “Determining the I²C Frequency Divider Ratio for SCL”. Note that the I²C Source Clock Frequency is half of the MPX clock frequency for MPC8641.
3. The maximum t_{I2DXKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. Guaranteed by design.
5. C_B = capacitance of one bus line in pF.

Figure 32 provides the AC test load for the I²C.

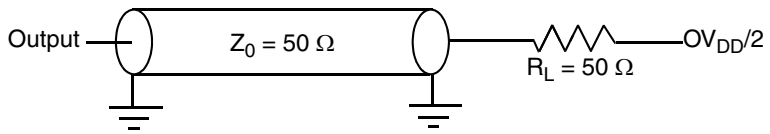

Figure 36. I²C AC Test Load

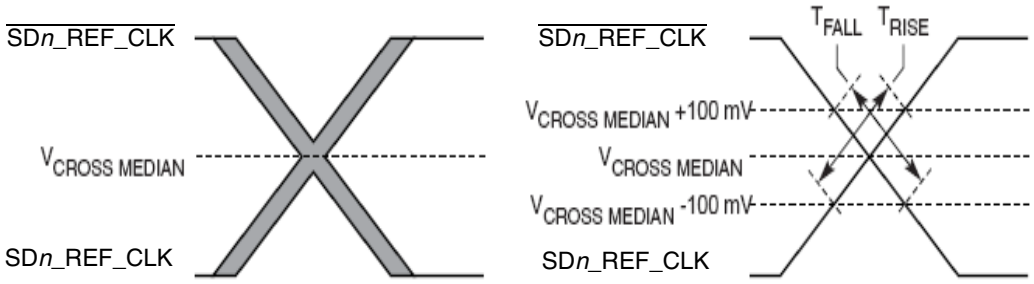

Figure 48. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes Reference Clocks is defined by each interface protocol based on application usage. Refer to the following sections for detailed information:

- Section 14.2, "AC Requirements for PCI Express SerDes Clocks"
- Section 15.2, "AC Requirements for Serial RapidIO SDn_REF_CLK and SDn_REF_CLK"

13.3 SerDes Transmitter and Receiver Reference Circuits

Figure 49 shows the reference circuits for SerDes data lane's transmitter and receiver.

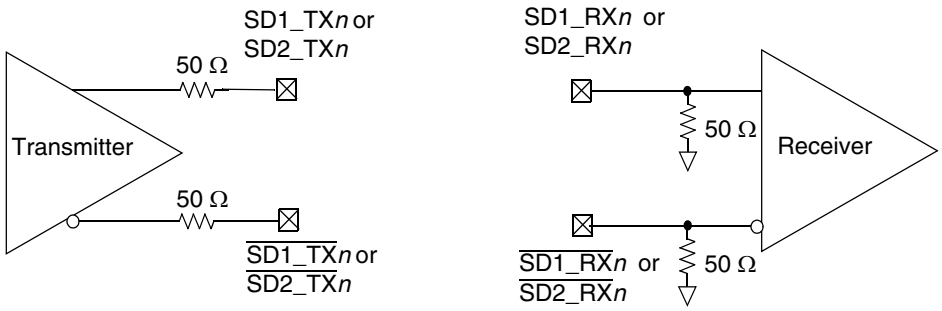

Figure 49. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express or Serial Rapid IO) in this document based on the application usage:"

- Section 14, "PCI Express"
- Section 15, "Serial RapidIO"

Note that external AC Coupling capacitor is required for the above two serial transmission protocols with the capacitor value defined in specification of each protocol section.

14 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8641.

Table 49. Differential Transmitter (TX) Output Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Units	Comments
T_{TX-EYE}	Minimum TX Eye Width	0.70	—	—	UI	The maximum Transmitter jitter can be derived as $T_{TX-MAX-JITTER}$ = 1 – T_{TX-EYE}= 0.3 UI. See Notes 2 and 3.
$T_{TX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median.	—	—	0.15	UI	Jitter is defined as the measurement variation of the crossing points ($V_{TX-DIFFp-p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2 and 3.
$T_{TX-RISE}$, $T_{TX-FALL}$	D+/D– TX Output Rise/Fall Time	0.125	—	—	UI	See Notes 2 and 5
$V_{TX-CM-ACp}$	RMS AC Peak Common Mode Output Voltage	—	—	20	mV	$V_{TX-CM-ACp}$ = RMS(|V_{TXD+} + V_{TXD-}|/2 – $V_{TX-CM-DC}$) $V_{TX-CM-DC}$ = $DC_{(avg)}$ of |V_{TX-D+} + V_{TX-D-}|/2 See Note 2
$V_{TX-CM-DC-ACTIVE-IDLE-DELTA}$	Absolute Delta of DC Common Mode Voltage During L0 and Electrical Idle	0	—	100	mV	|$V_{TX-CM-DC\ (during\ L0)}$ – $V_{TX-CM-Idle-DC\ (During\ Electrical\ Idle)}$|<=100 mV $V_{TX-CM-DC}$ = $DC_{(avg)}$ of |V_{TX-D+} + V_{TX-D-}|/2 [L0] $V_{TX-CM-Idle-DC}$ = $DC_{(avg)}$ of |V_{TX-D+} + V_{TX-D-}|/2 [Electrical Idle] See Note 2.
$V_{TX-CM-DC-LINE-DELTA}$	Absolute Delta of DC Common Mode between D+ and D–	0	—	25	mV	|$V_{TX-CM-DC-D+}$ – $V_{TX-CM-DC-D-}$| <= 25 mV $V_{TX-CM-DC-D+}$ = $DC_{(avg)}$ of |V_{TX-D+}| $V_{TX-CM-DC-D-}$ = $DC_{(avg)}$ of |V_{TX-D-}| See Note 2.
$V_{TX-IDLE-DIFFp}$	Electrical Idle differential Peak Output Voltage	0	—	20	mV	$V_{TX-IDLE-DIFFp}$ = |$V_{TX-IDLE-D+}$ –$V_{TX-IDLE-D-}$| <= 20 mV See Note 2.
$V_{TX-RCV-DETECT}$	The amount of voltage change allowed during Receiver Detection	—	—	600	mV	The total amount of voltage change that a transmitter can apply to sense whether a low impedance Receiver is present. See Note 6.
$V_{TX-DC-CM}$	The TX DC Common Mode Voltage	0	—	3.6	V	The allowed DC Common Mode voltage under any conditions. See Note 6.
$I_{TX-SHORT}$	TX Short Circuit Current Limit	—	—	90	mA	The total current the Transmitter can provide when shorted to its ground
$T_{TX-IDLE-MIN}$	Minimum time spent in Electrical Idle	50	—	—	UI	Minimum time a Transmitter must be in Electrical Idle Utilized by the Receiver to start looking for an Electrical Idle Exit after successfully receiving an Electrical Idle ordered set

14.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 50 is specified using the passive compliance/test measurement load (see Figure 52) in place of any real PCI Express interconnect + RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams will differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit will always be relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (that is, least squares and median deviation fits).

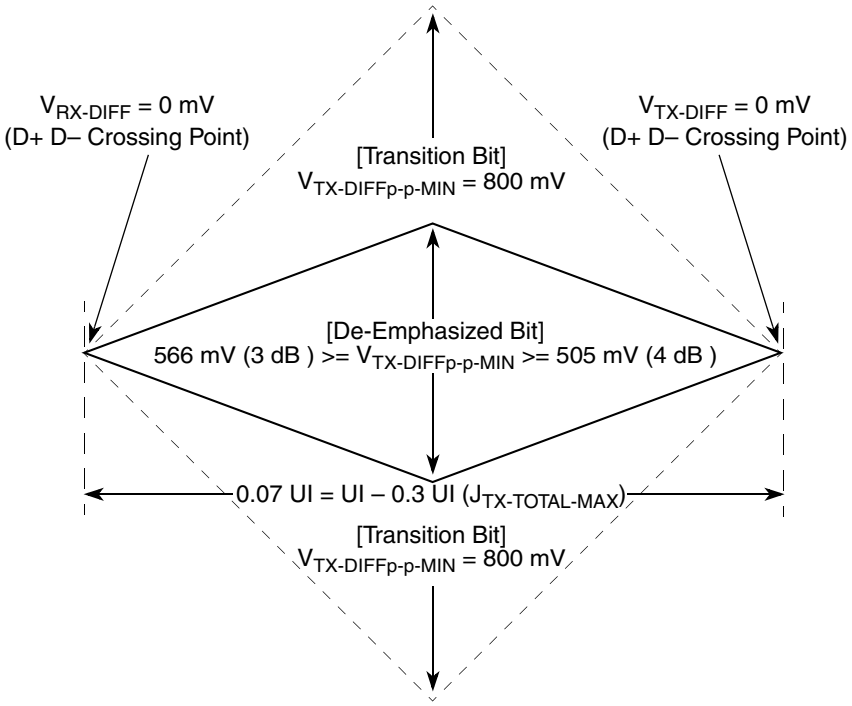

Figure 50. Minimum Transmitter Timing and Voltage Output Compliance Specifications

14.4.3 Differential Receiver (RX) Input Specifications

Table 50 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Table 50. Differential Receiver (RX) Input Specifications

Symbol	Parameter	Min	Nom	Max	Units	Comments
UI	Unit Interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for Spread Spectrum Clock dictated variations. See Note 1.
$V_{RX-DIFFp-p}$	Differential Peak-to-Peak Output Voltage	0.175	—	—	V	$V_{RX-DIFFp-p} = 2*\|V_{RX-D+} - V_{RX-D-}\|$ See Note 2.
T_{RX-EYE}	Minimum Receiver Eye Width	0.4	—	—	UI	The maximum interconnect media and Transmitter jitter that can be tolerated by the Receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.
$T_{RX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median.	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3 and 7.
$V_{RX-CM-ACp}$	AC Peak Common Mode Input Voltage	—	—	150	mV	$V_{RX-CM-ACp} = \|V_{RXD+} - V_{RXD-}\|/2 - V_{RX-CM-DC}$ $V_{RX-CM-DC} = DC_{(avg)}$ of $\|V_{RX-D+} - V_{RX-D-}\|/2$ See Note 2
$RL_{RX-DIFF}$	Differential Return Loss	15	—	—	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at +300 mV and –300 mV, respectively. See Note 4
RL_{RX-CM}	Common Mode Return Loss	6	—	—	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at 0 V. See Note 4
$Z_{RX-DIFF-DC}$	DC Differential Input Impedance	80	100	120	Ω	RX DC Differential mode impedance. See Note 5
Z_{RX-DC}	DC Input Impedance	40	50	60	Ω	Required RX D+ as well as D– DC Impedance (50 ± 20% tolerance). See Notes 2 and 5.
$Z_{RX-HIGH-IMP-DC}$	Powered Down DC Input Impedance	200 k	—	—	Ω	Required RX D+ as well as D– DC Impedance when the Receiver terminations do not have power. See Note 6.
$V_{RX-IDLE-DET-DIFFp-p}$	Electrical Idle Detect Threshold	65	—	—	mV	$V_{RX-IDLE-DET-DIFFp-p} = 2*\|V_{RX-D+} - V_{RX-D-}\|$ Measured at the package pins of the Receiver

Table 60. Receiver AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential Input Voltage	V_{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S_{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10^{-12}	—	—
Unit Interval	UI	400	400	ps	+/– 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 55. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

Table 61. Receiver AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential Input Voltage	V_{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S_{MI}	—	22	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10^{-12}	—	—
Unit Interval	UI	320	320	ps	+/– 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 55. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
$SENSEV_{SS}$_Core0	P14	Core0 GND sensing pin	—	31
$SENSEV_{SS}$_Core1	V20	Core1 GND sensing pin	—	12, 31, *S3*
$SENSEV_{DD}$_PLAT	N18	V_{DD}_PLAT sensing pin	—	28
$SENSEV_{SS}$_PLAT	P18	Platform GND sensing pin	—	29
$D1\_GV_{DD}$	B11, B14, D10, D13, F9, F12, H8, H11, H14, K10, K13, L8, P8, R6, U8, V6, W10, Y8, AA6, AB10, AC8, AD12, AE10, AF8, AG12, AH10, AJ8, AJ14, AK12, AL10, AL16	SDRAM 1 I/O supply	$D1\_GV_{DD}$ 2.5 - DDR 1.8 DDR2	—
$D2\_GV_{DD}$	B2, B5, B8, D4, D7, E2, F6, G4, H2, J6, K4, L2, M6, N4, P2, T4, U2, W4, Y2, AB4, AC2, AD6, AE4, AF2, AG6, AH4, AJ2, AK6, AL4, AM2	SDRAM 2 I/O supply	$D2\_GV_{DD}$ 2.5 V - DDR 1.8 V - DDR2	—
OV_{DD}	B22, B25, B28, D17, D24, D27, F19, F22, F26, F29, G17, H21, H24, K19, K23, M21, AM30	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, JTAG, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{DD} 3.3 V	—
LV_{DD}	AC20, AD23, AH22	TSEC1 and TSEC2 I/O voltage	LV_{DD} 2.5/3.3 V	—
TV_{DD}	AC17, AG18, AK20	TSEC3 and TSEC4 I/O voltage	TV_{DD} 2.5/3.3 V	—
SV_{DD}	H31, J29, K28, K32, L30, M28, M31, N29, R30, T31, U29, V32, W30, Y31, AA29, AB32, AC30, AD31, AE29, AG30, AH31, AJ29, AK32, AL30, AM31	Transceiver Power Supply SerDes	SV_{DD} 1.05/1.1 V	—
XV_{DD}_SRDS1	K26, L24, M27, N25, P26, R24, R28, T27, U25, V26	Serial I/O Power Supply for SerDes Port 1	XV_{DD}_SRDS1 1.05/1.1 V	—

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Wakefield Engineering 33 Bridge St. Pelham, NH 03076 Internet: www.wakefield.com	603-635-5102

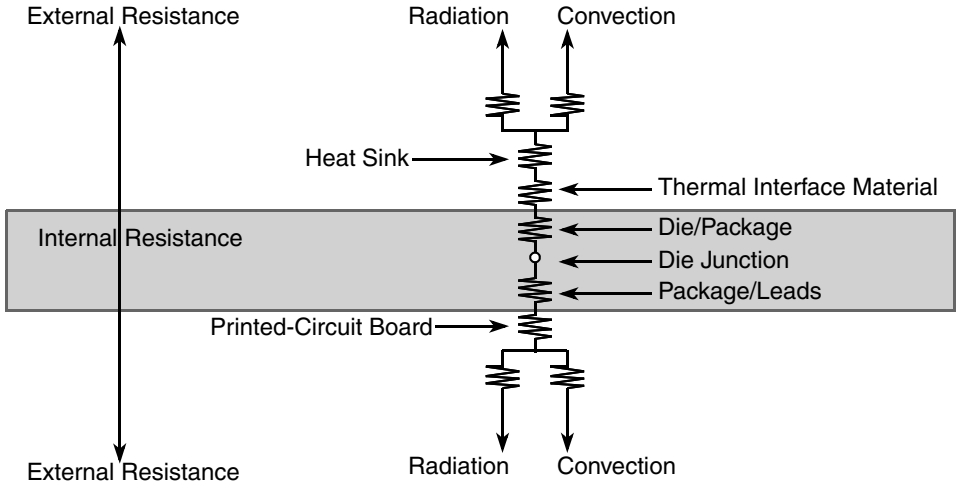
Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost.

19.2.1 Internal Package Conduction Resistance

For the exposed-die packaging technology described in Table 71, the intrinsic conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance (the case is actually the top of the exposed silicon die)
- The die junction-to-board thermal resistance

Figure 60 depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.



(Note the internal versus external package resistance.)

Figure 60. C4 Package with Heat Sink Mounted to a Printed-Circuit Board

Heat generated on the active side of the chip is conducted through the silicon, through the heat sink attach material (or thermal interface material), and finally to the heat sink where it is removed by forced-air convection.

Because the silicon thermal resistance is quite small, the temperature drop in the silicon may be neglected for a first-order analysis. Thus the thermal interface material and the heat sink conduction/convective thermal resistances are the dominant terms.

designer place at least one decoupling capacitor at each OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT pin of the device. These decoupling capacitors should receive their power from separate OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT planes, to enable quick recharging of the smaller chip capacitors. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

20.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}_SRDS*n*) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

20.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. In general all unused active low inputs should be tied to OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT, XV_{DD}_SRDS*n*, and SV_{DD} as required and unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Special cases:

DDR - If one of the DDR ports is not being used the power supply pins for that port can be connected to ground so that there is no need to connect the individual unused inputs of that port to ground. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port. Power supplies for other functional buses should remain powered.

For other pin pull-up or pull-down recommendations of signals, please see Section 17, "Signal Listings."

20.7 Output Buffer DC Impedance

The MPC8641 drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 66). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

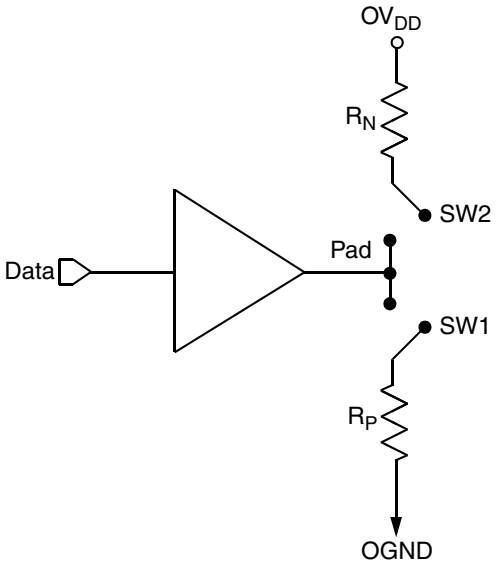


Figure 66. Driver Impedance Measurement

Table 73 summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 73. Impedance Characteristics

Impedance	DUART, Control, Configuration, Power Management	PCI Express	DDR DRAM	Symbol	Unit
R_N	43 Target	25 Target	20 Target	Z_0	W
R_P	43 Target	25 Target	20 Target	Z_0	W

Note: Nominal supply voltages. See Table 1, T_j = 105°C.